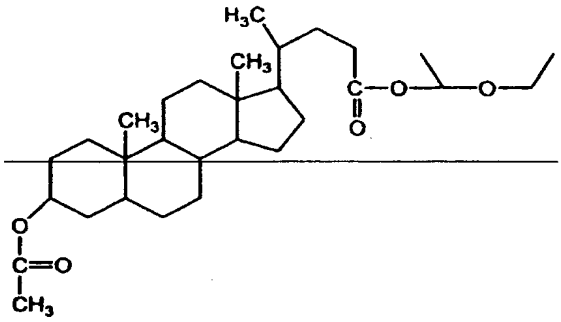
In the Claims:

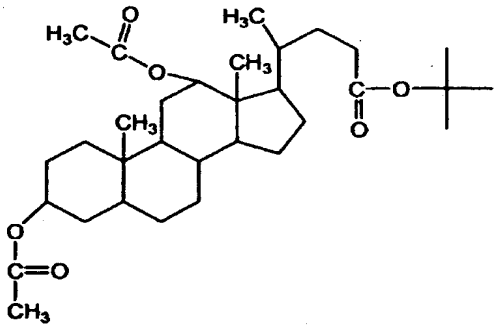
Please amend claims 1, 3 and 6, as follows:

Claim 1 (currently amended) An additive of following Formulas ~~3-7~~ 4 or 6 for a photoresist composition for a resist flow process:

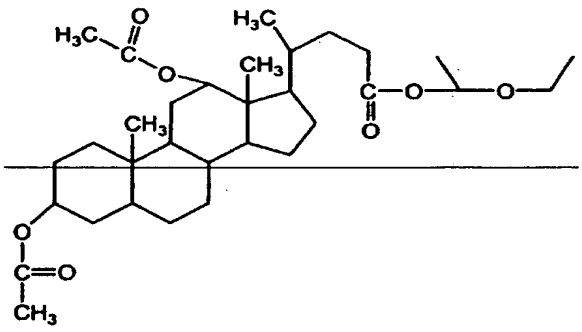
~~Formula 3~~



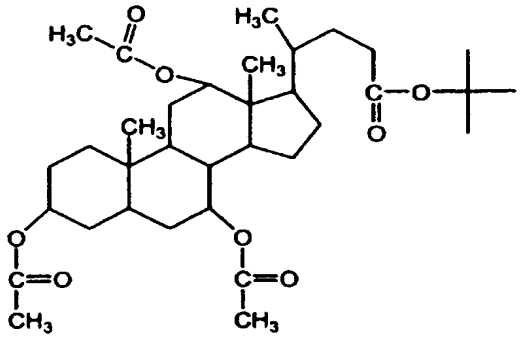
Formula 4



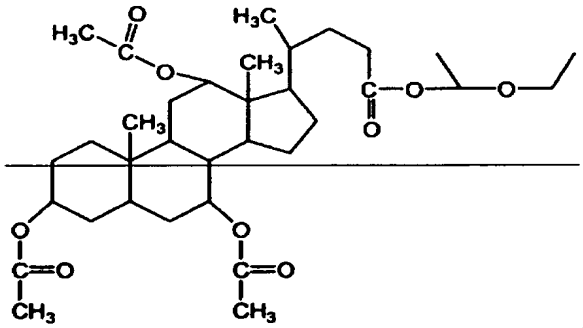
~~Formula 5~~



Formula 6



~~Formula 7~~

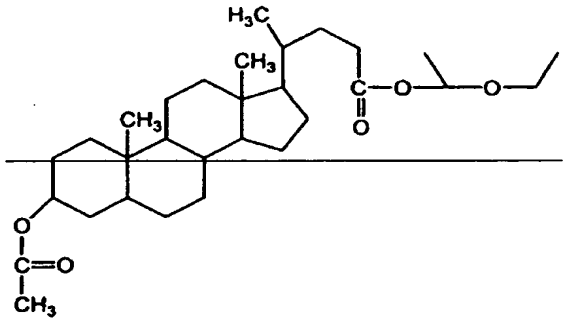


Claim 2 (previously canceled)

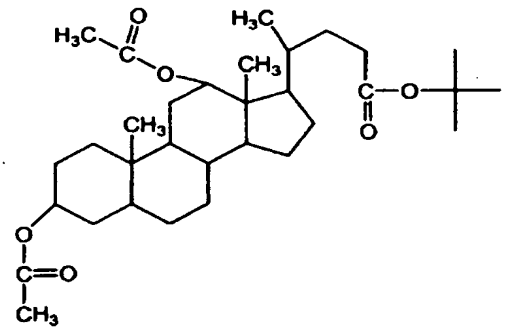
Claim 3 (currently amended) A photoresist composition comprising:

a photoresist polymer, a photoacid generator, an additive of following Formulas ~~3-7~~ 4 or 6, and an organic solvent,

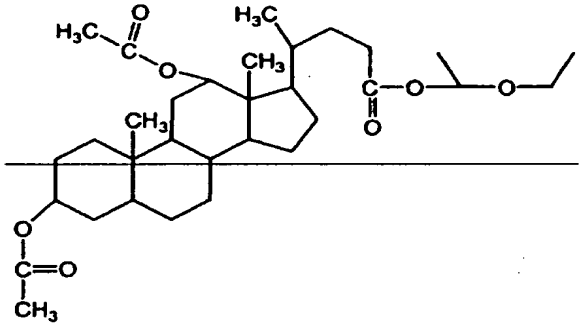
~~Formula 3~~



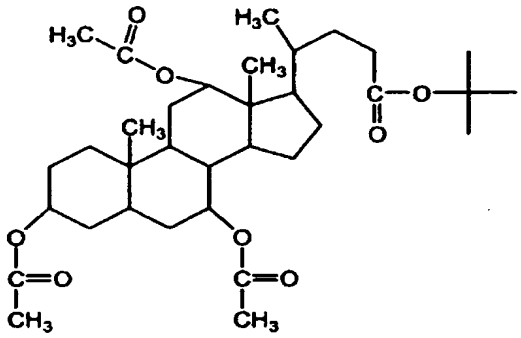
Formula 4



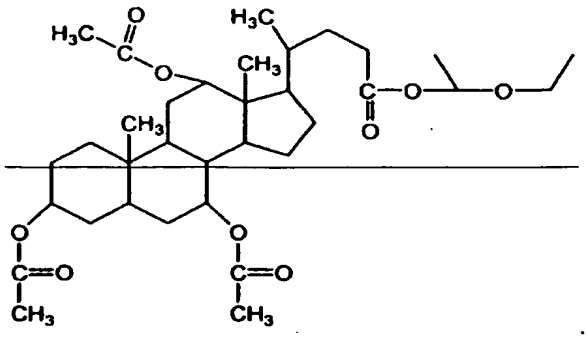
~~Formula 5~~



Formula 6



~~Formula 7~~

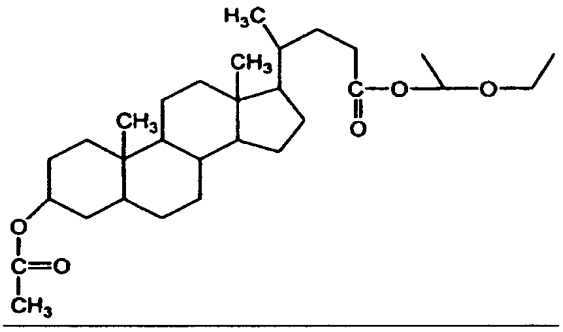


Claims 4-5 (previously canceled)

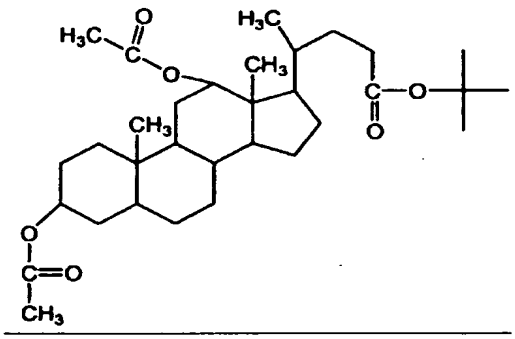
Claim 6 (currently amended) ~~The photoresist composition of claim 3~~ A photoresist composition comprising:

a photoresist polymer, a photoacid generator, an additive of following Formulas 3-7 and an organic solvent,

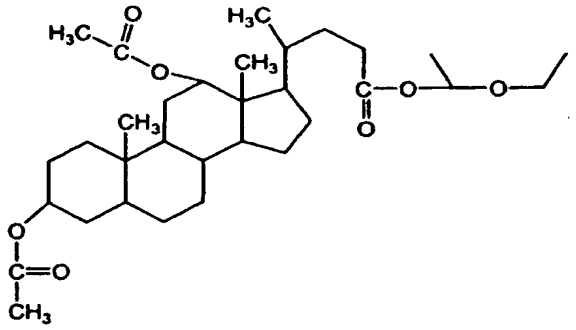
Formula 3



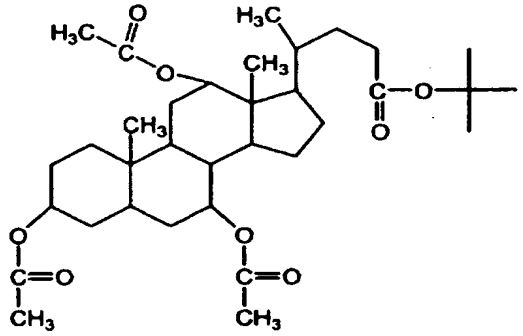
Formula 4



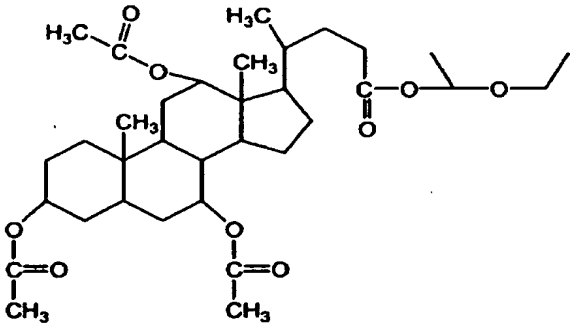
Formula 5



Formula 6



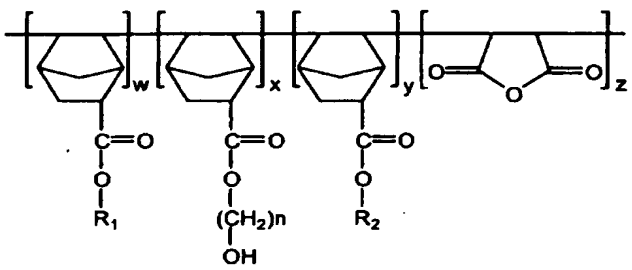
Formula 7



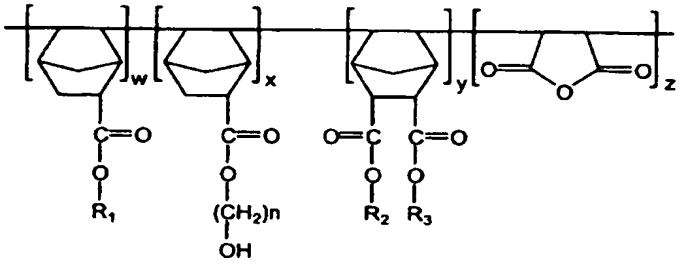
; and

wherein the photoresist polymer is a compound of following Formulas 8 or 9:

Formula 8



Formula 9



wherein, R_1 is and acid labile protecting group;

R_2 is hydrogen;

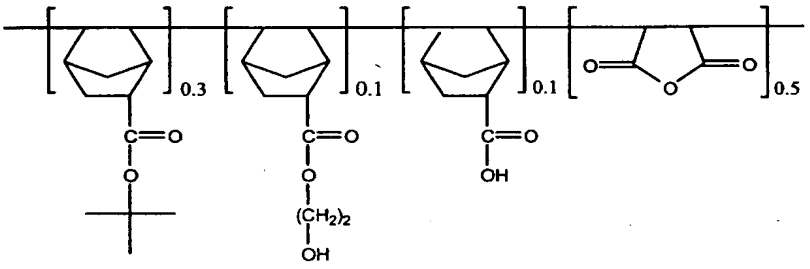
R_3 is hydrogen, selected from the group consisting of C_1-C_{10} alkyl, C_1-C_{10} alkoxyalkyl, and C_1-C_{10} alkyl containing at least one hydroxyl group (-OH);

n is an integer from 1 to 5; and

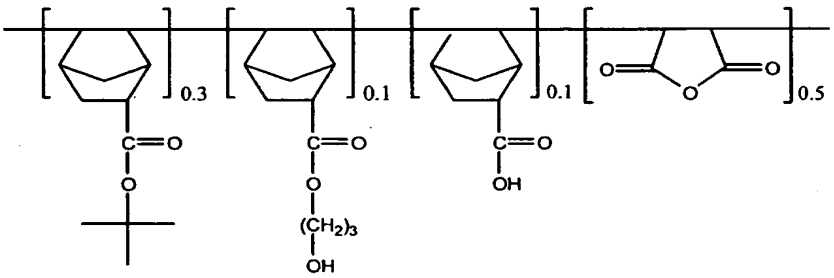
w, x, y and z individually denote the mole ratio of each monomer, preferably with proviso that w + x + y = 50mol%, and z is 50mol%.

Claim 7 (previously amended) The photoresist composition of claim 6 wherein the photoresist polymer is selected from the group consisting of compounds of following Formulas 10 to 13:

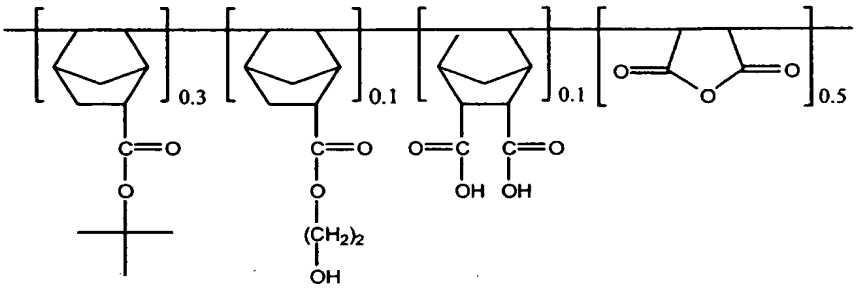
Formula 10



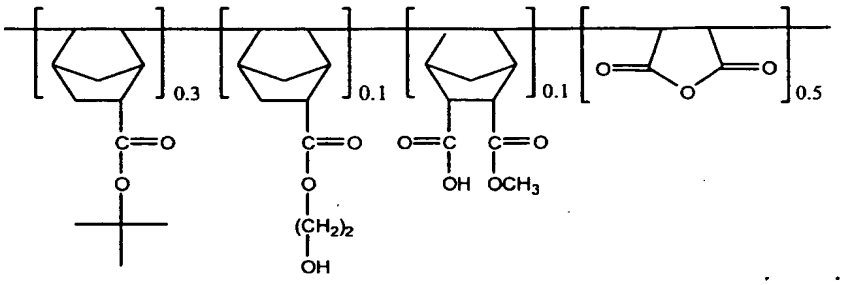
Formula 11



Formula 12



Formula 13



Claim 8 (original) The photoresist composition of claim 3 wherein the additive is present in an amount ranging from about 1 to about 70% by weight of the photoresist polymer.

Claim 9 (original) The photoresist composition of claim 3 wherein said photoacid generator is selected from the group consisting of diphenyl iodide hexafluorophosphate, diphenyl iodide hexafluoroarsenate, diphenyl iodide hexafluoroantimonate, diphenyl p-methoxyphenyl triflate, diphenyl p-toluenyl triflate, diphenyl p-isobutylphenyl triflate, diphenyl p-tert-butylphenyl triflate, triphenylsulfonium hexafluororphosphate, triphenylsulfonium hexafluoroarsenate, triphenylsulfonium hexafluoroantimonate, triphenylsulfonium triflate, dibutylnaphthylsulfonium triflate, and mixtures thereof .

Claim 10 (original) The photoresist composition of claim 3 wherein the photoacid generator is present in an amount ranging from about 0.01 to about 10% by weight of the photoresist polymer.

Claim 11 (original) The photoresist composition of claim 3 wherein the organic solvent is selected from the group consisting of propyleneglycol methyl ether acetate, ethyl lactate, methyl 3-methoxypropionate, ethyl 3-ethoxypropionate and cyclohexanone.

Claim 12 (original) The photoresist composition of claim 3 wherein the organic solvent is present in a range of from about 100 % to about 1000% by weight of the photoresist polymer.

Claims 13-20 (previously canceled)